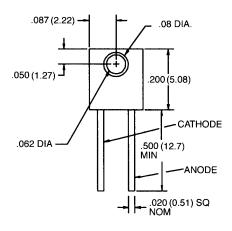
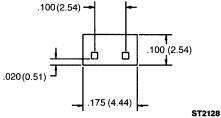


GaAs INFRARED EMITTING DIODE

QEE113

PACKAGE DIMENSIONS





NOTES:

- 1. DIMENSIONS ARE IN INCHES (mm).
 2. TOLERANCE IS ± .010 (.25)
 UNLESS OTHERWISE SPECIFIED.

DESCRIPTION

The QEE113 is a 940 nm GaAs LED encapsulated in a wide angle, orange, plastic sidelooker shell package.

FEATURES

- Tight production E₀ distribution with min/max limits.
- Steel lead frames for improved reliability in solder mounting.
- Good optical-to-mechanical alignment.
- Mechanically and wavelength matched to QSE11X series phototransistor.
- Plastic package color allows easy recognition from phototransistor.
- High irradiance level.



GaAs INFRARED EMITTING DIODE

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C Unless Otherwise Specified)	
Storage Temperature	
Operating Temperature	
Lead Temperature (Iron)	260°C for 10 sec. (2,3,5)
Continuous Forward Current	5.0 Volts
Power Dissipation	100 mW

ELECTRICAL CHARACTERISTICS (T _A = 25°C Unless Otherwise Specified) (All measurements made under pulse conditions.)							
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS	
Forward Voltage	V _F	_		1.50	V	I _F = 20 mA	
Reverse Leakage Current	l _e			10	μΑ	V _R = 5.0 V	
Peak Emission Wavelength	λ _P	_	940	_	nm	I _F = 20 mA	
Emission Angle at ½ Power	θ		±25	_	Degrees		
Radiant Incidence	E₀	0.015		-	mW/10° Cone	$I_F = 20 \text{ mA}^{(6.7)}$	

NOTES

- 1. Derate power dissipation linearly 1.33 mW/°C above 25°C.
- 2. RMA flux is recommended.
- Methanol or Isopropyl alcohols are recommended as cleaning agents.
 Soldering iron tip 1/4" (1.6 mm) minimum from housing.
 As long as leads are not under any stress or spring tension.

- 6. Measurement is taken at the end of a single 100 μsec pulse.
- 7. E_θ is a measurement of the average apertured radiant energy incident upon a sensing area 0.444" (11.3 mm) in diameter, perpendicular to and centered on the mechanical axis of the lens, and 2.54" (64.4 mm) from the measurement surface. E_θ is not necessarily uniform within the measurement area.